

High Frequency High Voltage Diode**PST HV 37-08F****Characteristics**

1. High junction temperature up to 130°C
2. Low forward voltage drop, and small current leakage
3. Avalanche breakdown protection
4. Max reverse recovery time to 70nS
5. Excellent properties against HV surge impact
6. Axial leading wires which are weldable
7. Epoxy package with anti-corrosion properties on surface

Application

- Rectification for microwave oven
- Industrial microwave power supplies
- HF X ray source
- Laser power supply
- Voltage multiplying circuits



- Rectification of power supplies for other electronic devices

1. Main Specification

No.	Item	Symbol	Unit	Rating	Conditions
1	Repetitive Peak Reverse Voltage	V _{RRM}	KV	8	
2	Average Forward Current	I _{F (AV)}	mA	200	T _{amb} =60 °C 50HZ Sine-half Wave Rectification Average Value
3	Forward Surge Current	I _{FSM}	A	15	T _{amb} =25 °C 50HZ Sine-half Wave,One Shot
4	Reverse Surge Current	I _{RSM}	μ A	5	
5	Maximum Junction Temperature	T _{jmax}	°C	130	
6	Storage Temperature	T _{stg}	°C	-40~+130	

2. Electric Specification

NO.	Item	Symbol	Unit	Rating	Test conditions
1	Forward Voltage Drop	V _{FM}	V	18max	I _{FM} =200mA
2	Normal Temperature Reverse Current	I _{RM1}	μ A	5max	V _{RM} =8KV



3	High Temperature Reverse Current	I_{RM2}	μA	t_{max}	Tamb=100°C $V_{RM}=8KV$
4	Reverse Breakdown Voltage	V_Z	KV	8	$I_R=200mA$
5	Reverse Recovery Time	trr	nS	70	$I_F=2mA, I_{RM}=4mA$ 90%

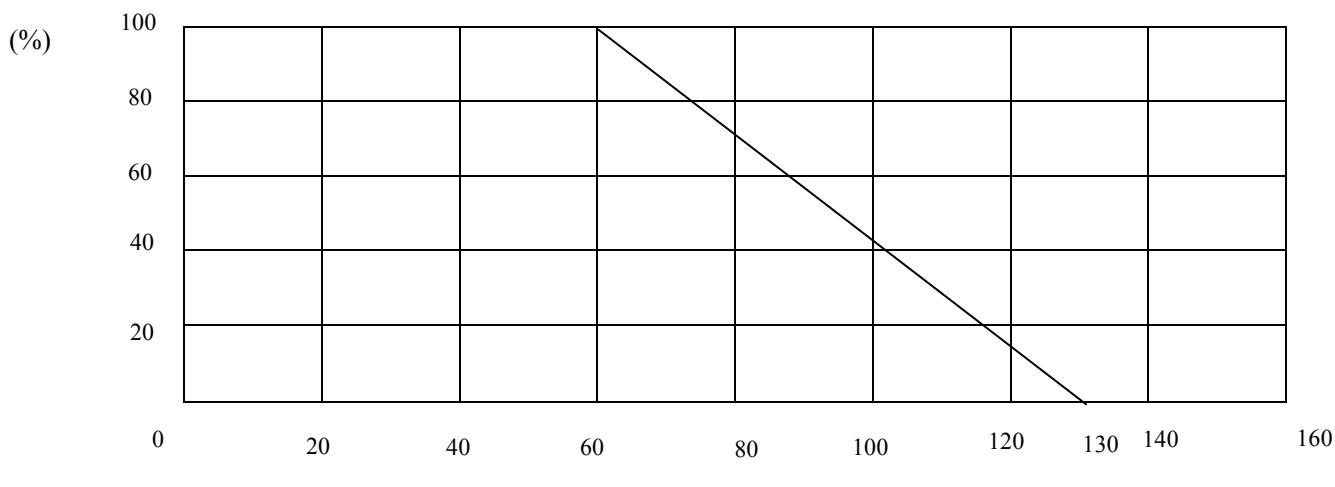
(Tamb=25 °C, unless otherwise specified)

3. Application

For high voltage rectification;

4. Derating of Forward Current

Ratio to rating



Ambient temperature (°C)

On condition of provision of a fin on cathode side and air cooling)



5. Dimensions (in mm)